NL17SG34

Single Buffer

The NL17SG34 MiniGate™ is an advanced high−speed CMOS Buffer in ultra−small footprint.

The NL17SG34 input structures provides protection when voltages up to 4.6 V are applied.

Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: t_{PD} = 2.3 ns (Typ) at V_{CC} = 3.0 V, C_L = 15 pF
- Low Power Dissipation: I_{CC} = 0.5 μA (Max) at T_A = 25°C
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
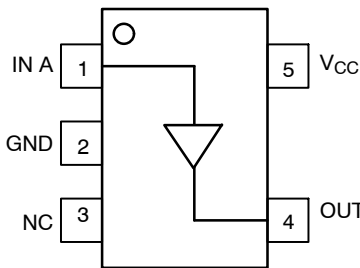- Ultra−Small Packages
- These are Pb−Free and Halide−Free Devices
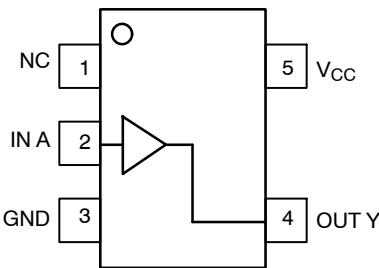

Figure 1. SOT−953
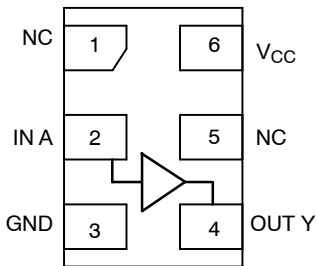(Top Thru View)

Figure 2. SC−88A/TSOP−5
(Top View)

Figure 3. UDFN
(Top View)
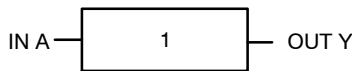
Figure 4. Logic Symbol

ON Semiconductor®
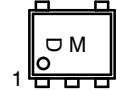
http://onsemi.com
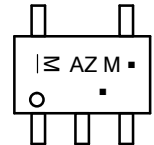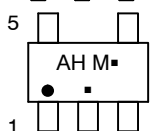
PIN ASSIGNMENT

	SOT−953	SC88A/TSOP5	UDFN6
1	IN A	NC	NC
2	GND	IN A	IN A
3	NC	GND	GND
4	OUT Y	OUT Y	OUT Y
5	V_{CC}	V_{CC}	NC
6			V_{CC}

FUNCTION TABLE

A Input	Y Output
L	L
H	H

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NL17SG34

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +5.5	V
V_{IN}	DC Input Voltage		−0.5 to +4.6	V
V_{OUT}	DC Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	−0.5 to V_{CC} +0.5 −0.5 to +4.6	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−20	mA
I_{OUT}	DC Output Source/Sink Current		±20	mA
I_{CC}	DC Supply Current per Supply Pin		±20	mA
I_{GND}	DC Ground Current per Ground Pin		±20	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		0.9	3.6	V
V_{IN}	Digital Input Voltage		0.0	3.6	V
V_{OUT}	Output Voltage	Output at High or Low State Power−Down Mode (V_{CC} = 0 V)	0.0 0.0	V_{CC} 3.6	V
T_A	Operating Temperature Range		−55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate	V_{CC} = 3.3 V ± 0.3 V	0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

NL17SG34

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions		V_{CC} (V)	T_A = 25°C		T_A = −55°C to +125°C		Unit
					Min	Max	Min	Max	
V_{IH}	High−Level Input Voltage			0.9	V_{CC}		V_{CC}		V
				1.1 to 1.3	$0.7 \times V_{CC}$		$0.7 \times V_{CC}$		
				1.4 to 1.6	$0.65 \times V_{CC}$		$0.65 \times V_{CC}$		
				1.65 to 1.95	$0.65 \times V_{CC}$		$0.65 \times V_{CC}$		
				2.3 to 2.7	1.7		1.7		
				3.0 to 3.6	2.0		2.0		
V_{IL}	Low−Level Input Voltage			0.9		GND		GND	V
				1.1 to 1.3		$0.3 \times V_{CC}$		$0.3 \times V_{CC}$	
				1.4 to 1.6		$0.35 \times V_{CC}$		$0.35 \times V_{CC}$	
				1.65 to 1.95		$0.35 \times V_{CC}$		$0.35 \times V_{CC}$	
				2.3 to 2.7		0.7		0.7	
				3.0 to 3.6		0.8		0.8	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −20 µA	0.9	0.75		0.75		V
			I_{OH} = −0.3 mA	1.1 to 1.3	$0.75 \times V_{CC}$		$0.75 \times V_{CC}$		
			I_{OH} = −1.7 mA	1.4 to 1.6	$0.75 \times V_{CC}$		$0.75 \times V_{CC}$		
			I_{OH} = −3.0 mA	1.65 to 1.95	Vcc−0.45		Vcc−0.45		
			I_{OH} = −4.0 mA	2.3 to 2.7	2.0		2.0		
			I_{OH} = −8.0 mA	3.0 to 3.6	2.48		2.48		
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20 µA	0.9		0.1		0.1	V
			I_{OL} = 0.3 mA	1.1 to 1.3		$0.25 \times V_{CC}$		$0.25 \times V_{CC}$	
			I_{OL} = 1.7 mA	1.4 to 1.6		$0.25 \times V_{CC}$		$0.25 \times V_{CC}$	
			I_{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	
			I_{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	
			I_{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	
I_{IN}	Input Leakage Current	$0 \leq V_{IN} \leq 3.6$ V		0 to 3.6		± 0.1		± 1.0	µA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND		3.6		0.5		10.0	µA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NL17SG34

AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0$ ns

Symbol	Parameter	Test Condition	V_{CC} (V)	T_A = 25° C			T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A to Y	$C_L = 10$ pF, $R_L = 1$ MΩ	0.9	–	12.6	15.3	–	19.0	ns
			1.1 to 1.3	–	8.7	13.4	–	15.2	
			1.4 to 1.6	–	4.9	8.5	–	10.0	
			1.65 to 1.95	–	3.8	6.2	–	6.7	
			2.3 to 2.7	–	2.6	3.9	–	4.4	
			3.0 to 3.6	–	2.1	3.1	–	3.7	
		$C_L = 15$ pF, $R_L = 1$ MΩ	0.9	–	13.0	16.6	–	20.8	ns
			1.1 to 1.3	–	8.0	12.5	–	15.7	
			1.4 to 1.6	–	5.4	9.3	–	11.2	
			1.65 to 1.95	–	4.2	6.9	–	7.1	
			2.3 to 2.7	–	2.8	4.4	–	5.0	
			3.0 to 3.6	–	2.3	3.4	–	3.9	
		$C_L = 30$ pF, $R_L = 1$ MΩ	0.9	–	14.5	17.6	–	22.4	ns
			1.1 to 1.3	–	9.5	13.5	–	18.8	
			1.4 to 1.6	–	7.4	11.1	–	15.9	
			1.65 to 1.95	–	5.6	9.2	–	9.6	
			2.3 to 2.7	–	3.7	5.7	–	6.1	
			3.0 to 3.6	–	2.9	4.4	–	4.8	
C_{IN}	Input Capacitance		0 to 3.6		3	–	–	–	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	–	4		–	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.
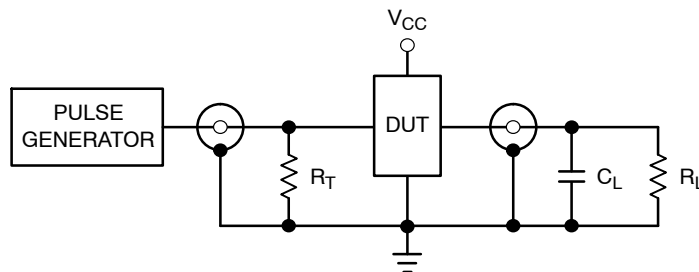
NL17SG34
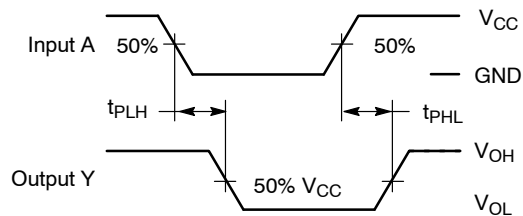
Figure 5. Switching Waveforms

$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping†
NL17SG34P5T5G	SOT–953 (Pb–Free)	8000 / Tape & Reel
NL17SG34DFT2G	SC–88A (Pb–Free)	3000 / Tape & Reel
NL17SG34DTT1G*	TSOP–5 (Pb–Free)	3000 / Tape & Reel
NL17SG34AMUTCG*	UDFN6 1.45x1 mm (Pb–Free)	3000 / Tape & Reel
NL17SG34CMUTCG*	UDFN6 1x1 mm (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging
 Specifications Brochure, BRD8011/D.
*In Development

MiniGate is a trademark of Semiconductor Components Industries, LLC (SCILLC).

SC−88A (SC−70−5/SOT−353)
CASE 419A−02
ISSUE M

DATE 11 APR 2023

SCALE 2:1

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. 419A−01 OBSOLETE. NEW STANDARD 419A−02
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

5X b

⊕ 0.2 Ⓜ B Ⓜ

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.80	0.95	1.10
A1	---	---	0.10
A3	0.20 REF		
b	0.10	0.20	0.30
c	0.10	---	0.25
D	1.80	2.00	2.20
E	2.00	2.10	2.20
E1	1.15	1.25	1.35
e	0.65 BSC		
L	0.10	0.15	0.30

RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC MARKING
DIAGRAM***

XXXM∎

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "∎", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code
M   = Date Code
∎   = Pb−Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	98ASB42984B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SC−88A (SC−70−5/SOT−353)**		**PAGE 1 OF 1**

UDFN6, 1.45x1.0, 0.5P
CASE 517AQ
ISSUE O
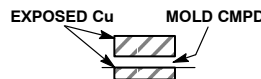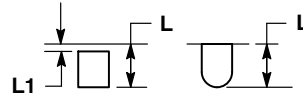
SCALE 4:1

DATE 15 MAY 2008

TOP VIEW

PIN ONE
REFERENCE

| 0.10 | C |

| 0.10 | C |

SIDE VIEW

DETAIL B

6X | 0.05 | C |

| 0.05 | C |

BOTTOM VIEW

DETAIL A

| ⊕ | 0.10 | C | A | B |
| | 0.05 | C | NOTE 3 |

DETAIL A
OPTIONAL
CONSTRUCTIONS

DETAIL B
OPTIONAL
CONSTRUCTIONS

EXPOSED Cu   MOLD CMPD

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

| DIM | MILLIMETERS | |
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
E	1.00 BSC	
e	0.50 BSC	
L	0.30	0.40
L1	---	0.15

MOUNTING FOOTPRINT
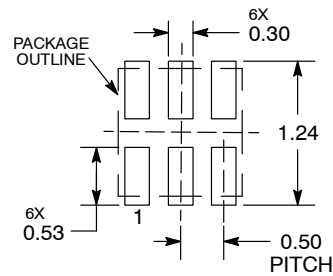
PACKAGE
OUTLINE

6X
0.30

1.24

6X
0.53

0.50
PITCH

DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***

XM

X   = Specific Device Code
M   = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪ ", may or may not be present.

DOCUMENT NUMBER:	**98AON30313E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**UDFN6, 1.45x1.0, 0.5P**		**PAGE 1 OF 1**

ON Semiconductor®

SOT−953
CASE 527AE
ISSUE E

DATE 02 AUG 2011
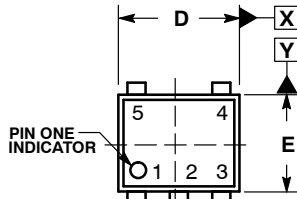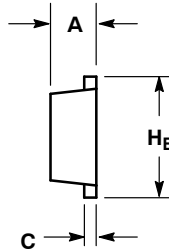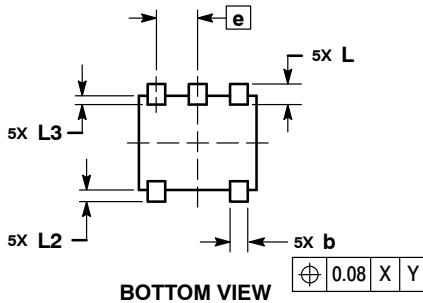
SCALE 4:1

TOP VIEW

PIN ONE INDICATOR

SIDE VIEW

BOTTOM VIEW

⊕ | 0.08 | X | Y

SOLDERING FOOTPRINT*

5X 0.20

5X 0.35

PACKAGE OUTLINE

1.20

0.35 PITCH

DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H$_E$	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	---	---	0.15

GENERIC MARKING DIAGRAM*

XM
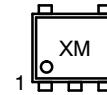
X = Specific Device Code
M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, "G" or microdot " ▪", may or may not be present.

DOCUMENT NUMBER:	98AON26457D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOT−953	PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

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